

AMENDMENTS TO THE SPECIFICATION:

Please replace paragraph [0024] with the following amended paragraph:

[0024] Doped mesa 23 is then removed using ~~using~~ a mask that is substantially the inverse of the mask used to form doped mesa 23. The material of doped mesa 23 is etched using known etching techniques. This inverse mask (not shown) is also used to etch passivation layer 20, which is etched using reactive ion etching with a methyl ion source, to form via 2519 as shown in Figure 7. A layer of nickel 24 followed by a layer of gold 25 is then deposited and patterned as shown in Figure 8. Nickel layer 24 serves as a diffusion barrier to prevent diffusion of gold into layers 16, 18 and 20. Gold layer 25 is then used as a seed site for selective deposit of Indium to form Indium layer 26 as shown in Figure 8 using known techniques. Thus the completed detector 10 is formed.

Please replace paragraph [0027] with the following amended paragraph:

[0027] Although specific embodiments are disclosed herein, they are not to be construed as limiting the scope of the present invention. Many variants of the present invention will become apparent to those skilled in the art in light of the teaching of this specification. For example, via 2519 may be part of an elongated column lead to provide contact to a linear group of detector cells. The scope of the invention is only limited by the claims appended hereto.